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(12) **United States Design Patent** (10) **Patent No.:** **US D859,334 S**
Yokoyama et al. (45) **Date of Patent:** **** Sep. 10, 2019**

(54) **SEMICONDUCTOR DEVICE**

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(**) Term: **15 Years**

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(52) **U.S. Cl.**
USPC **D13/182**

(58) **Field of Classification Search**
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H05K 1/182; H05K 1/026; H05K 1/0228;
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1/0263

See application file for complete search history.

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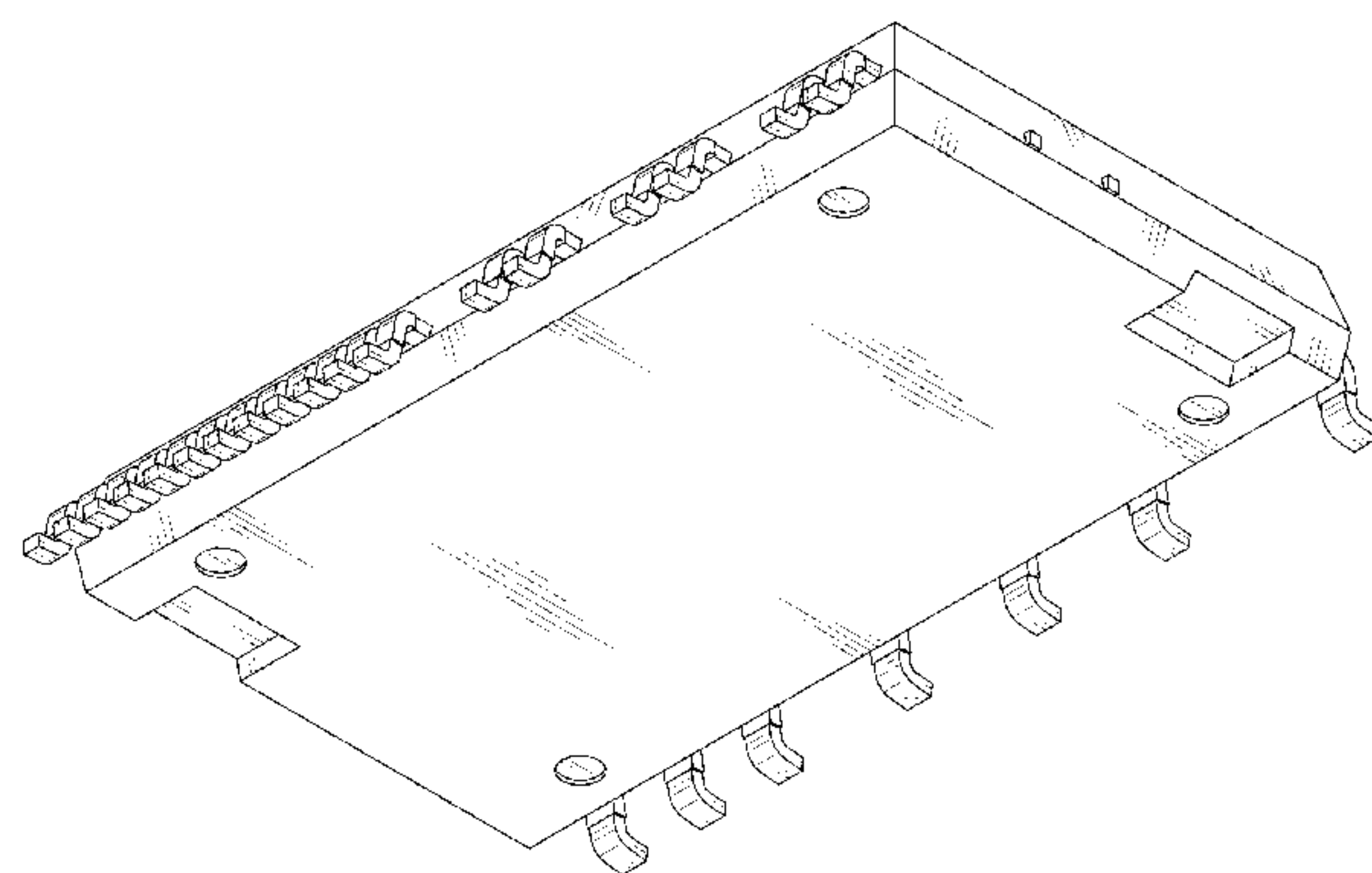
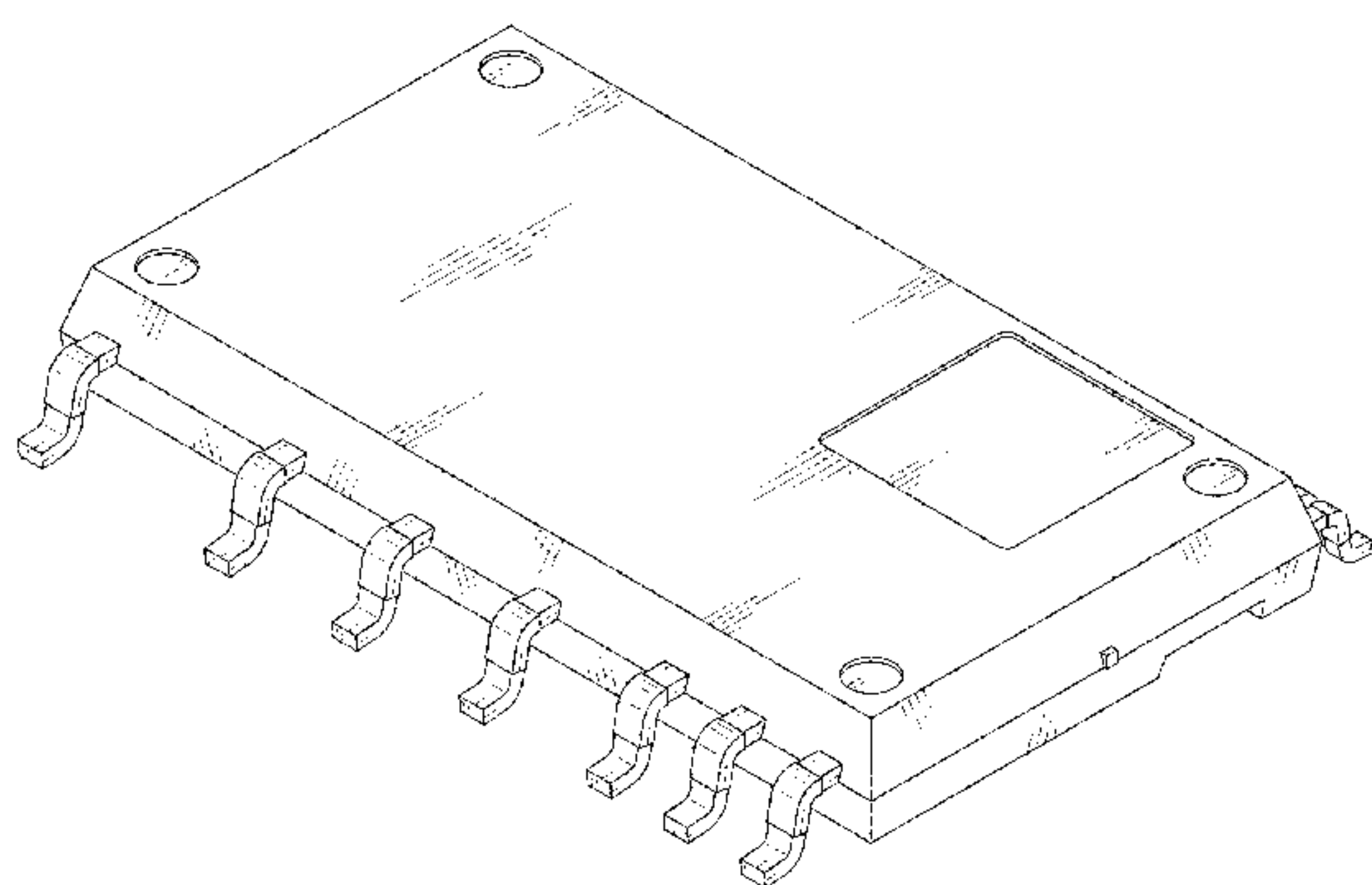
(57) **CLAIM**

The ornamental design for a semiconductor device, as shown and described.

DESCRIPTION

FIG. 1 is a front, bottom and right side perspective view of a semiconductor device showing our new design;
FIG. 2 is a rear, top and left side perspective view thereof;
FIG. 3 is a front view thereof;
FIG. 4 is a rear view thereof;
FIG. 5 is a top view thereof;
FIG. 6 is a bottom view thereof;
FIG. 7 is a left side view thereof; and,
FIG. 8 is a right side view thereof.

1 Claim, 6 Drawing Sheets



(56)

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Fig. 1

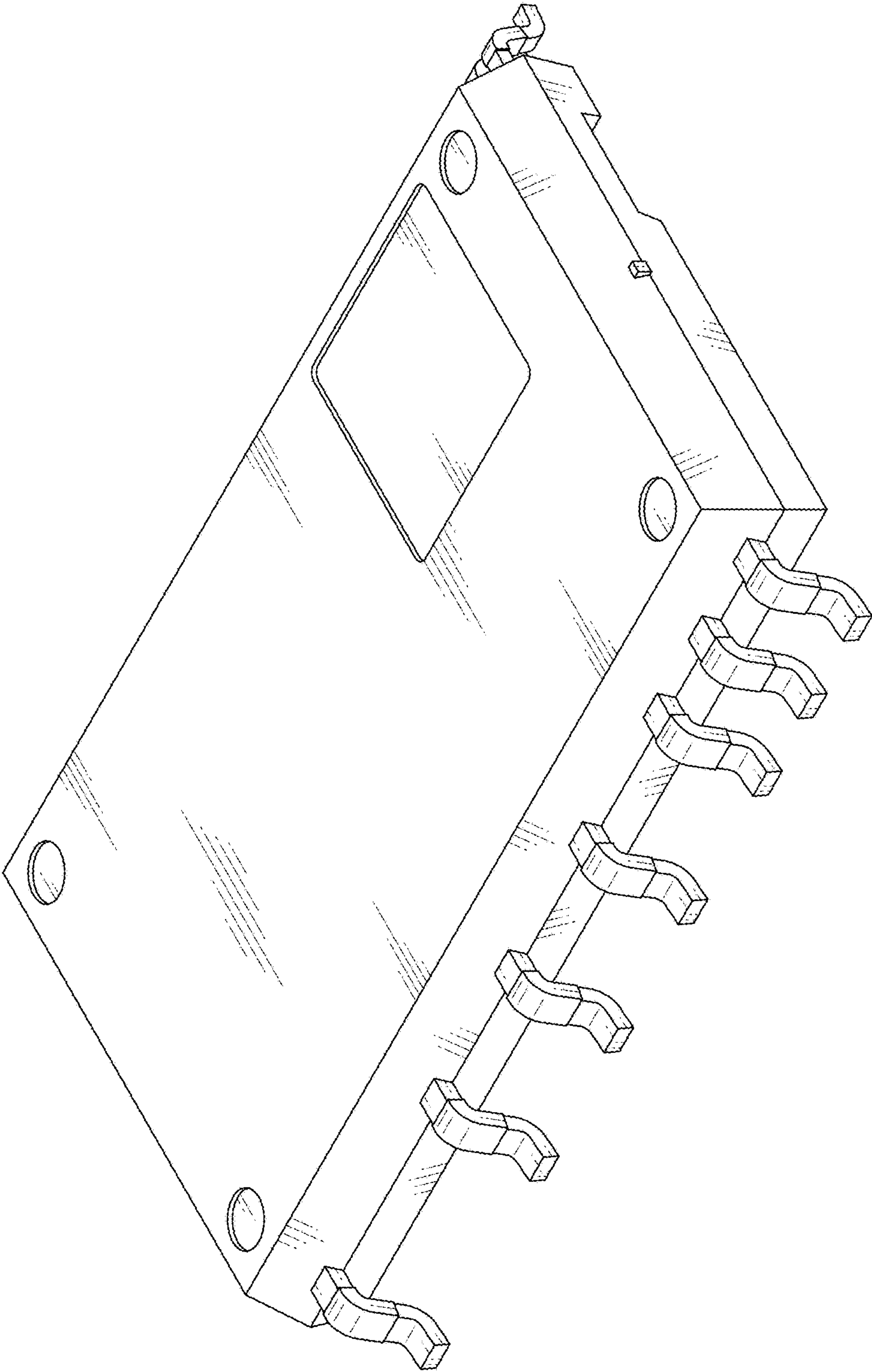


Fig. 2

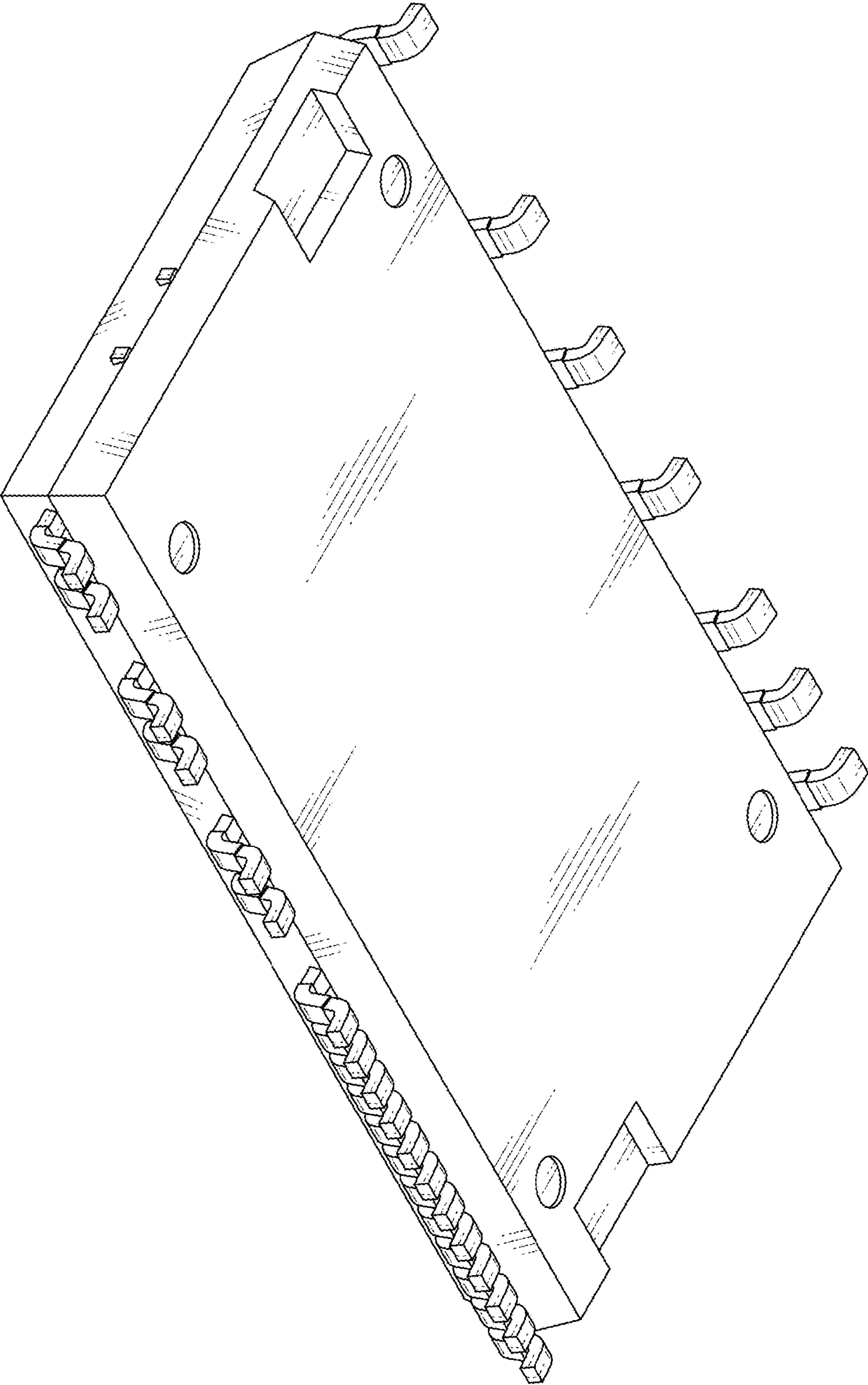


Fig. 3

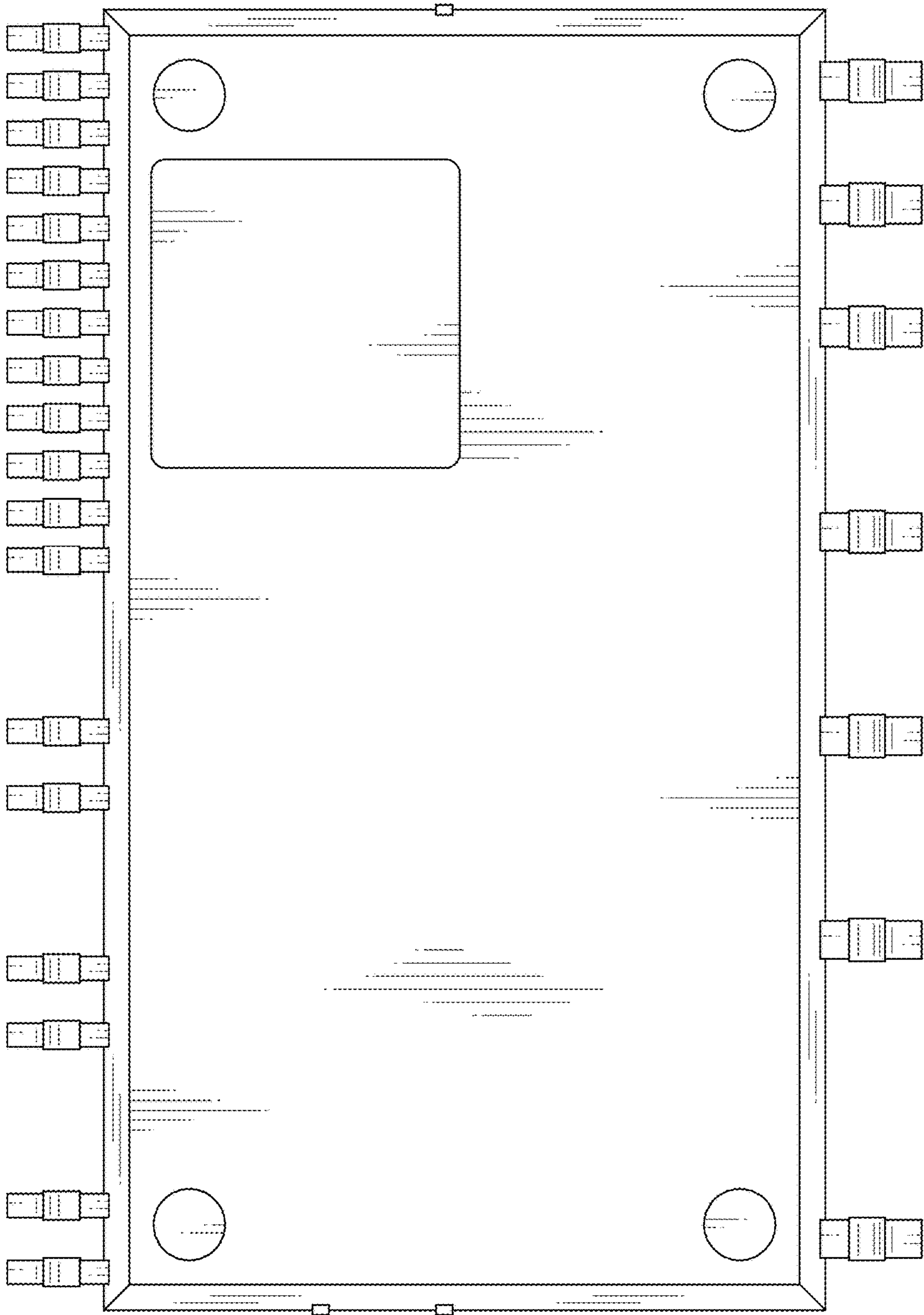


Fig. 4

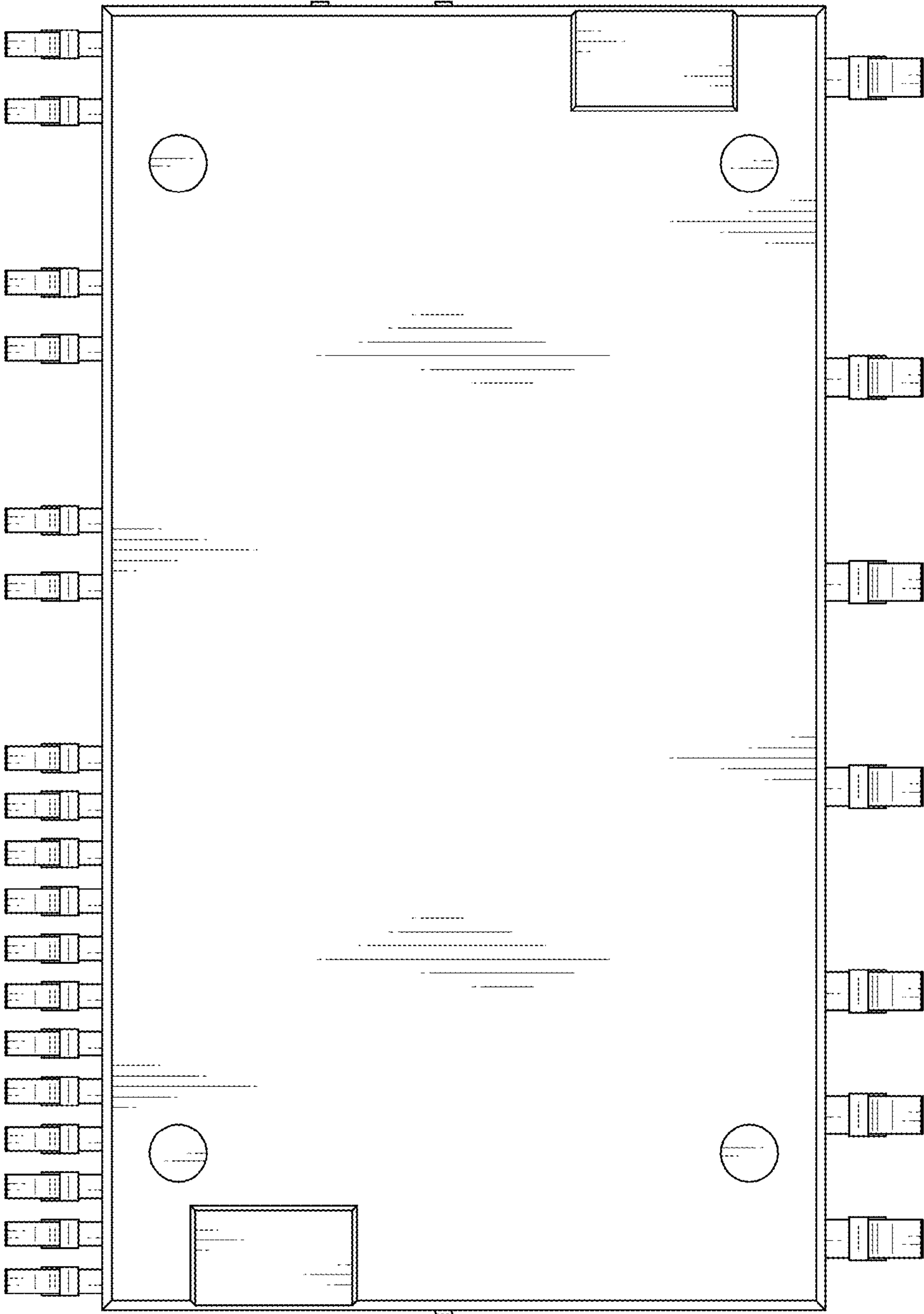


Fig. 5

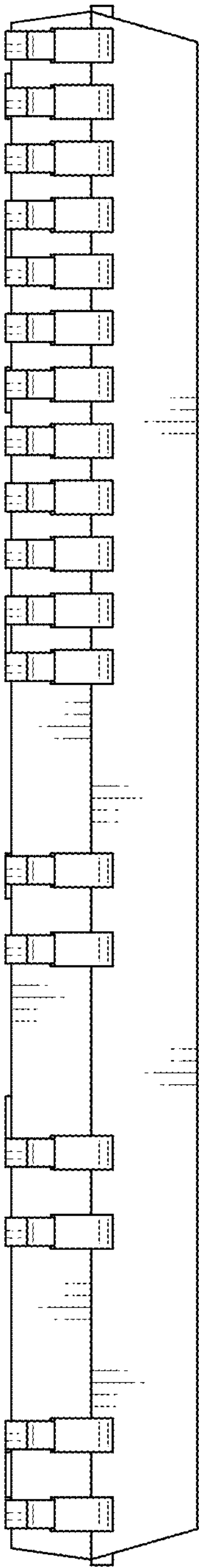


Fig. 6

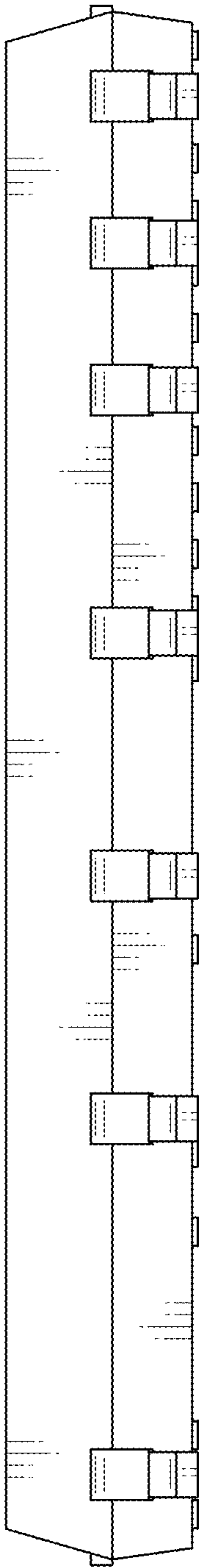


Fig. 8

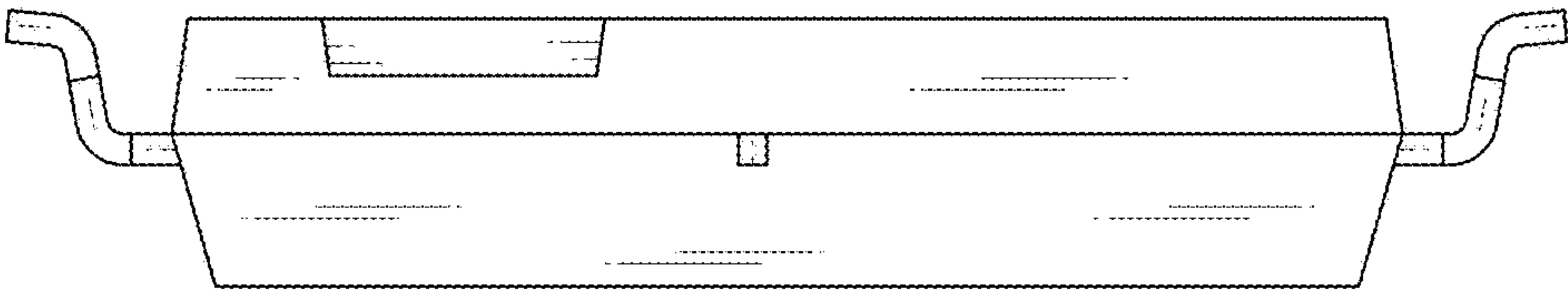


Fig. 7

